

次世代赤外線天文衛星 SPICA 搭載用 遠赤外線観測装置 SAFARI

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SAFARI

SPICA: space mission for mid- & far-IR astronomy

- Telescope: 2.5 m & <8 K

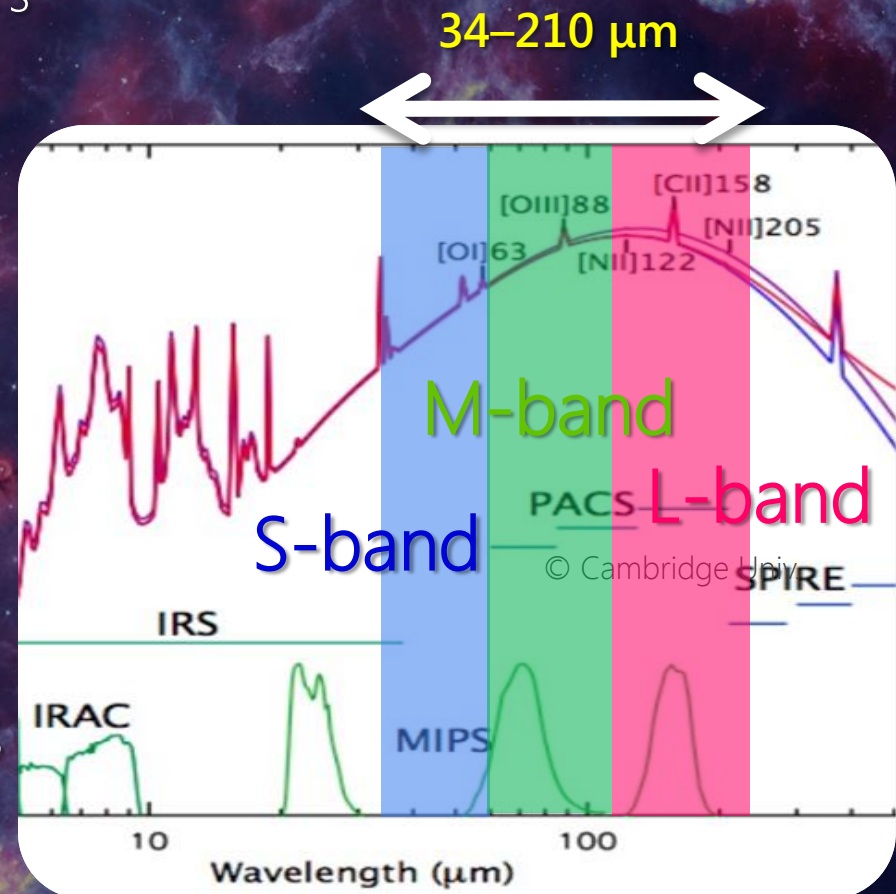
 - Natural background limited Infrared (IR) observations
→ Need **ultra-sensitive** IR detectors

- IR instruments

 - SMI (12-37 μm)

 - SAFARI (34-210 μm)

 - Three-band grating spectrometers with **TES bolometer** arrays



Noise Equivalent Power (NEP) required by SPICA/SAFARI

Minimum detectable input power to have
 $S/N=1$ with $T_{\text{int}}=0.5$ sec

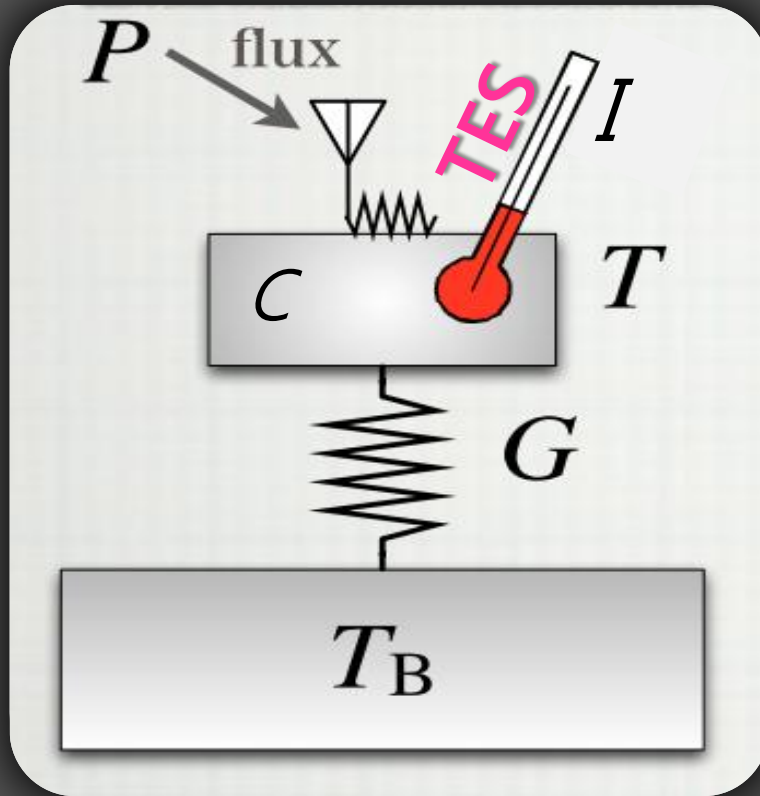
Higher sensitivity = Lower NEP

ISO-Herschel era
 $\sim 10^{-16} - 10^{-17}$ W/ $\sqrt{\text{Hz}}$

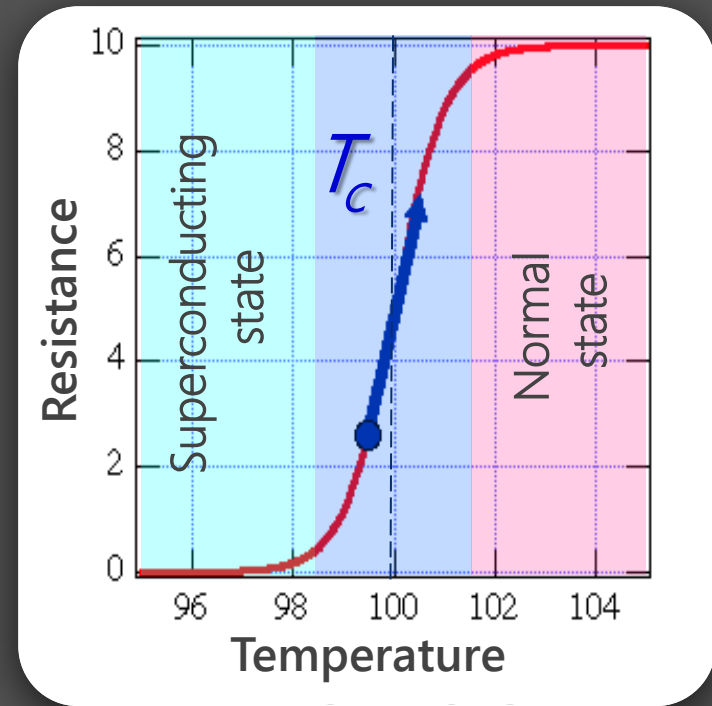
100-1000 times!!

SPICA/SAFARI
 2×10^{-19} W/ $\sqrt{\text{Hz}}$

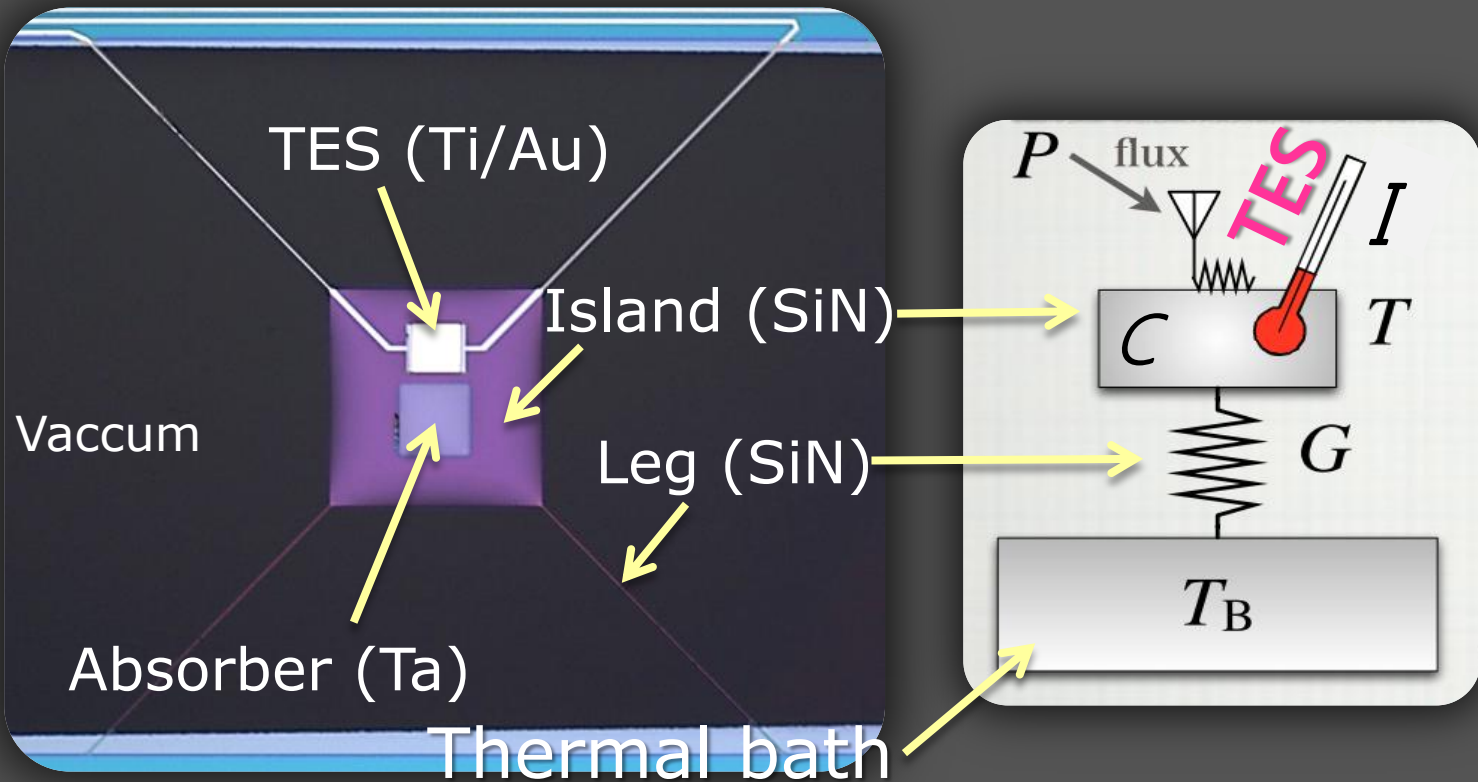
Transition Edge Sensors (TESs)



$$\Delta P \rightarrow \Delta T \rightarrow \Delta R$$



Typical TES pixel for SAFARI/S-band



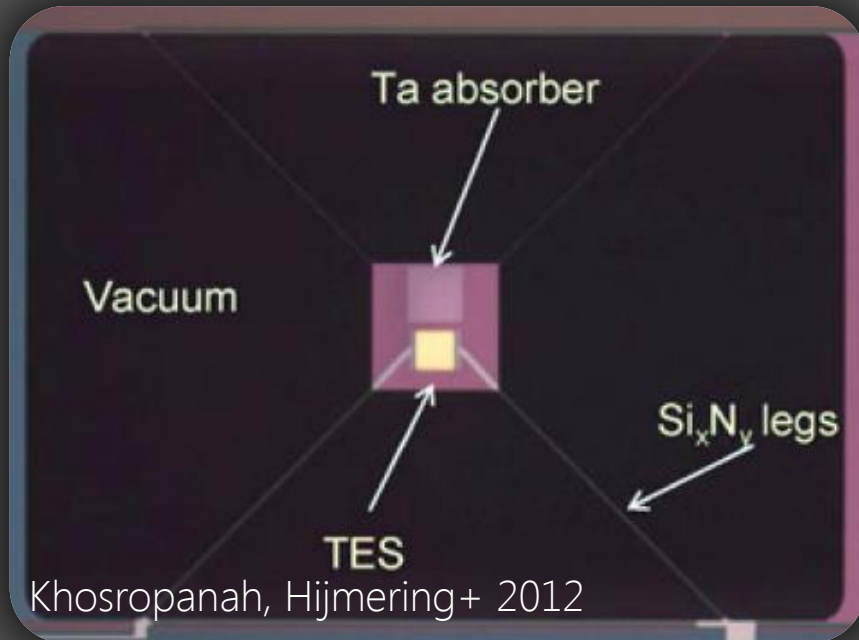
Intrinsic noise = phonon noise

$$\rightarrow \text{Noise Equivalent Power (NEP}_{\text{ph}}) \propto \sqrt{G}$$



Long-standing questions (1)

SRON-TEEs fabricated by **KOH wet-etching**



SiN legs

- Width (W) = 1 μm
- Thickness (T) = 0.5 μm
- Length (L) = 400 μm

$$G_{\text{meas}} = 330 \text{ fW/K}$$

$$\text{NEP}_{\text{meas}} = 4.2 \times 10^{-19} \text{ W}/\sqrt{\text{Hz}} \text{ (best)}$$

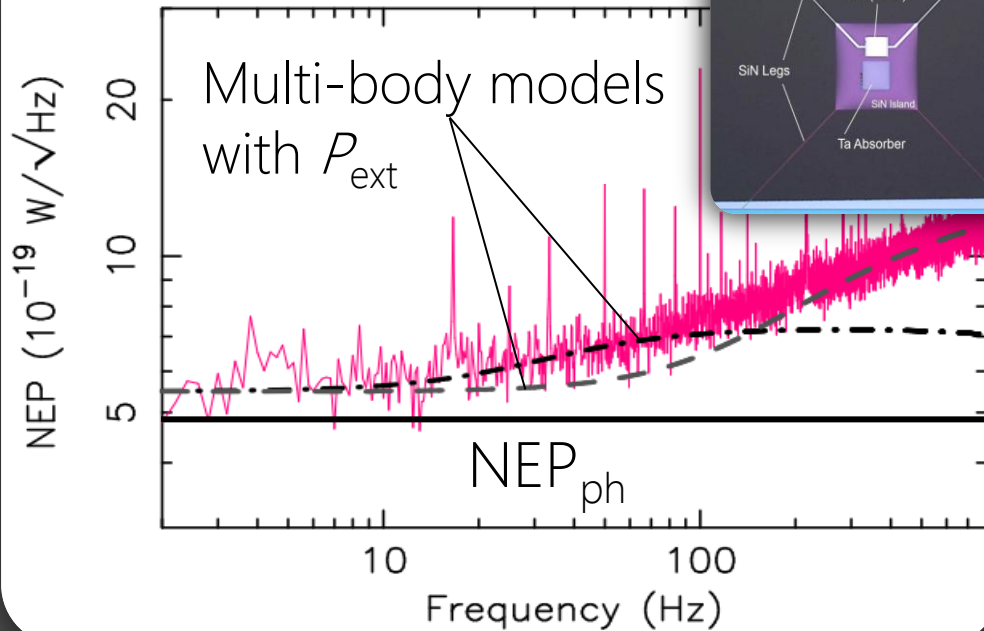
→ Deep Reactive Ion Etching (**DRIE**)

Q1. Can we achieve lower G and thus NEP values by making **narrower and thinner SiN legs**??



Long-standing questions (2)

Suzuki+2014



$$NEP_{\text{meas}}/NEP_{\text{ph}} \sim 2-3 \text{ (typ.)}$$

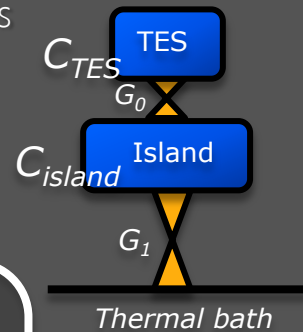
Khosropanah, Hijmering+ 09,10,11,12

Excess noises

1) Extra-phonon noise ($f > \sim 10\text{Hz}$)

$$C_{\text{tes}} \sim C_{\text{island}} \ \& \ C_{\text{legs}}$$

2) Photon noise



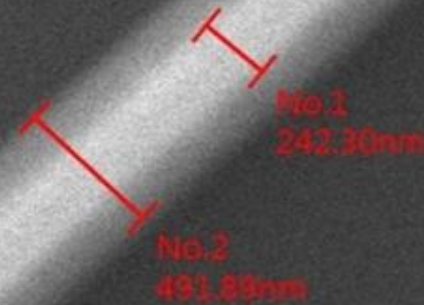
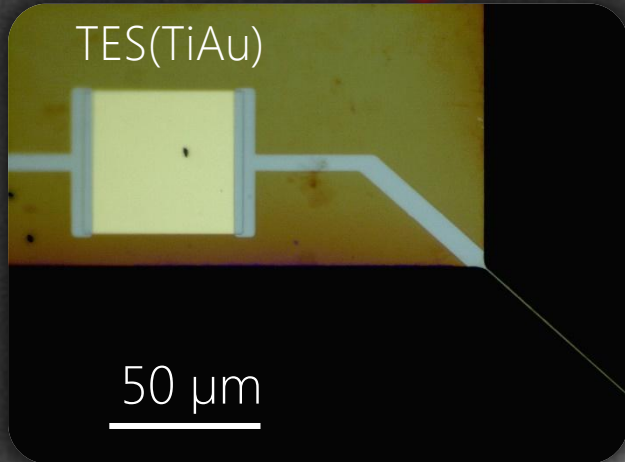
Q2. Can we reduce the extra-phonon noise by making **lighter SiN island** and **SiN legs**??

Q3. **How dark** is our setup??

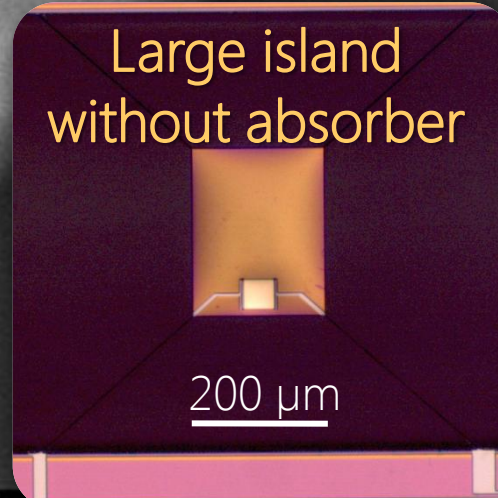


New TESs fabricated by DRIE

- Deep Reactive Ion Etching (DRIE) process success
- Narrow SiN legs $\sim 0.5\text{-}0.7\ \mu\text{m}$
- Thin SiN legs and island $\sim 0.2\ \mu\text{m}$



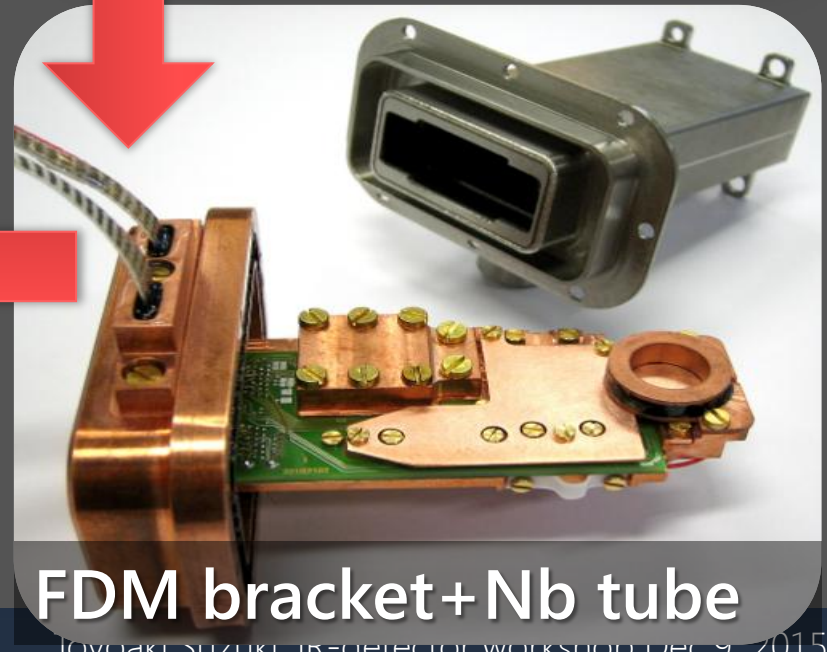
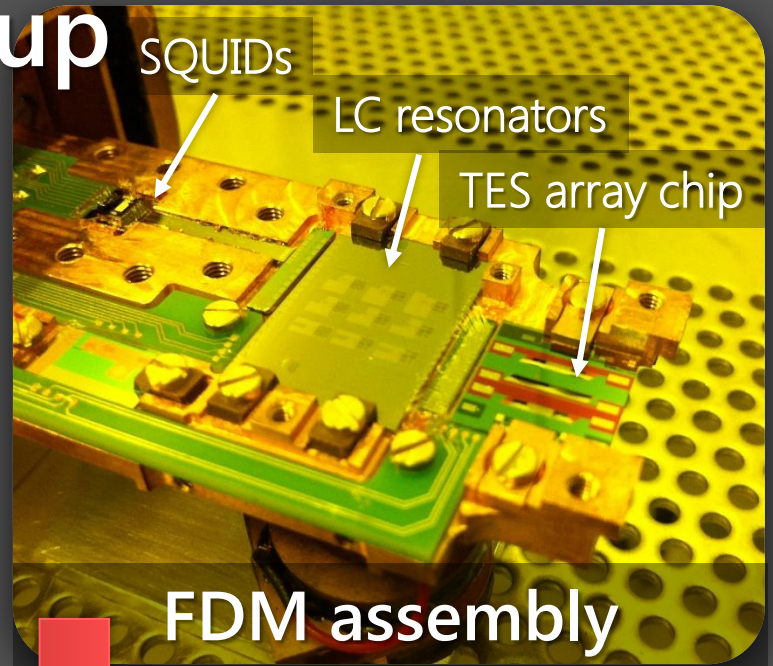
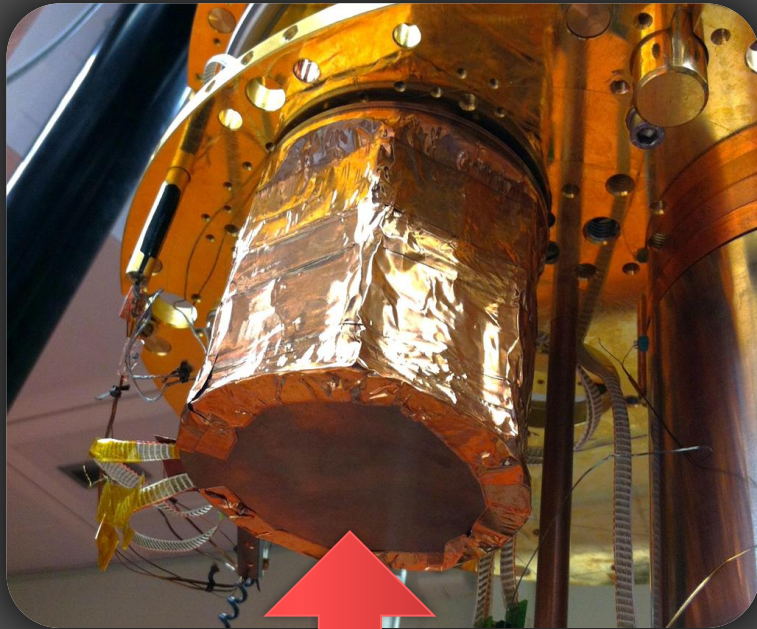
Fabricated by Marcel Ridder (SRON)



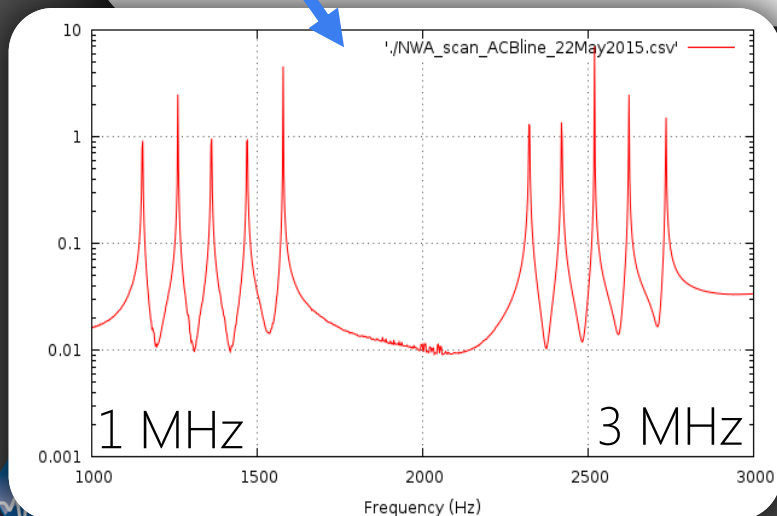
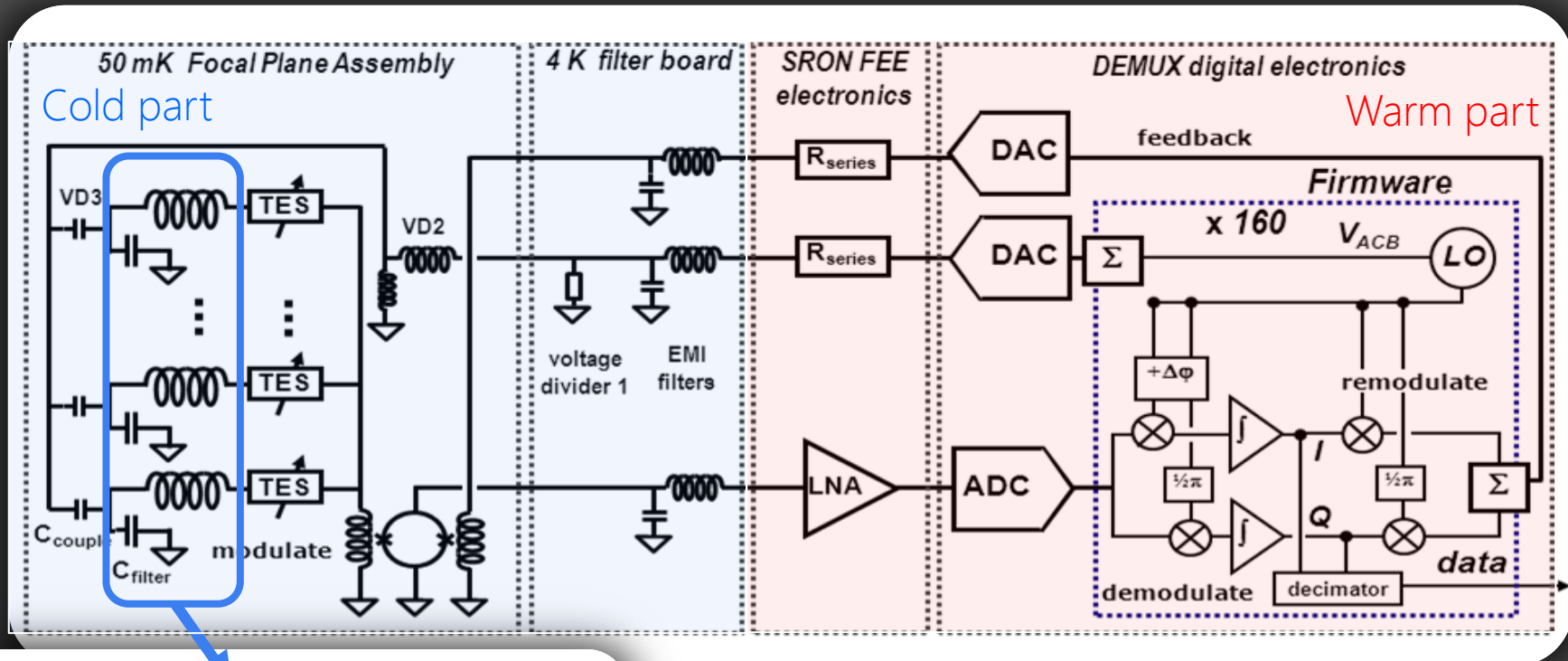
Do not blow a puff of air, please!!



AC measurement setup

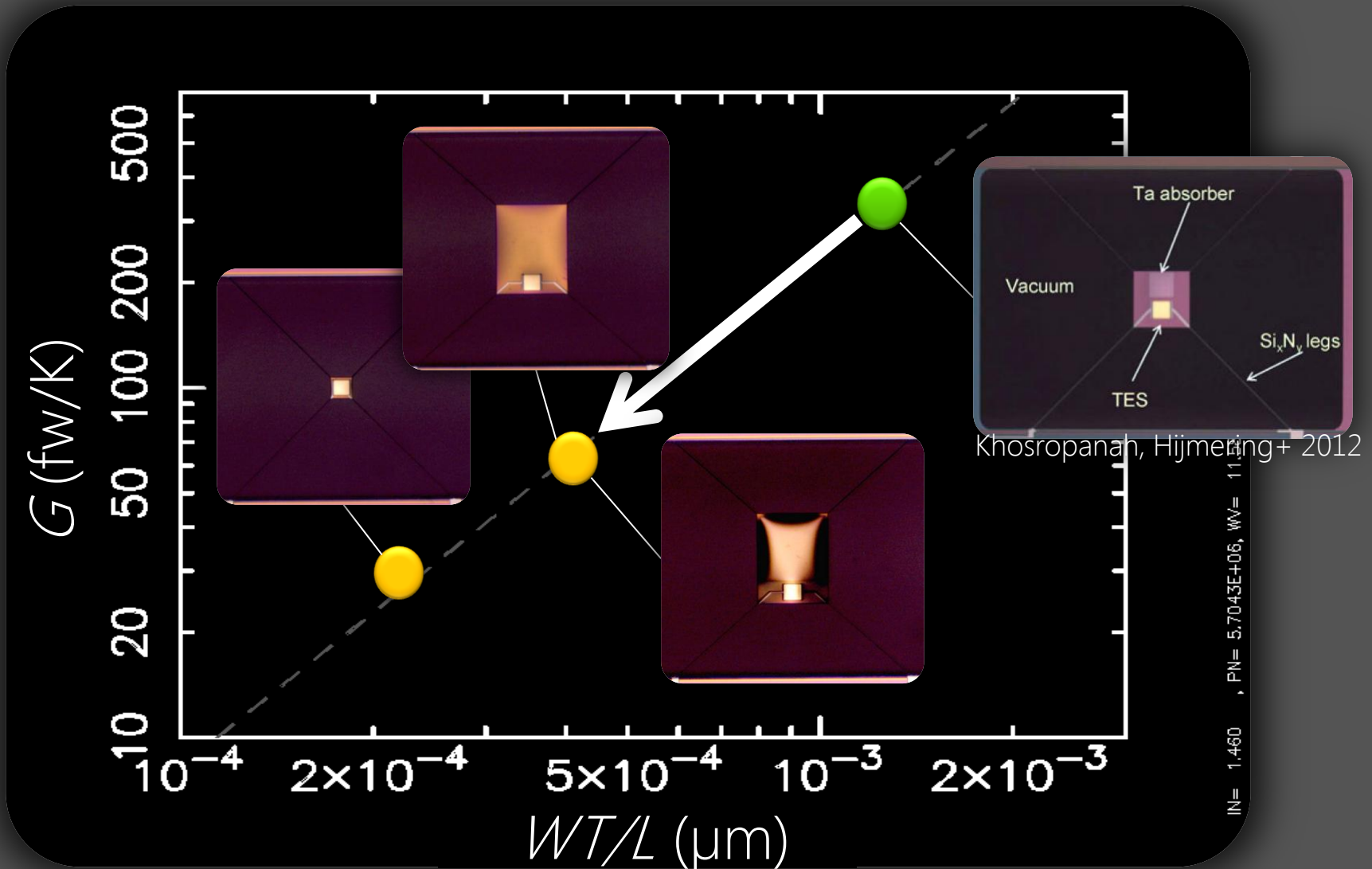


FDM readout

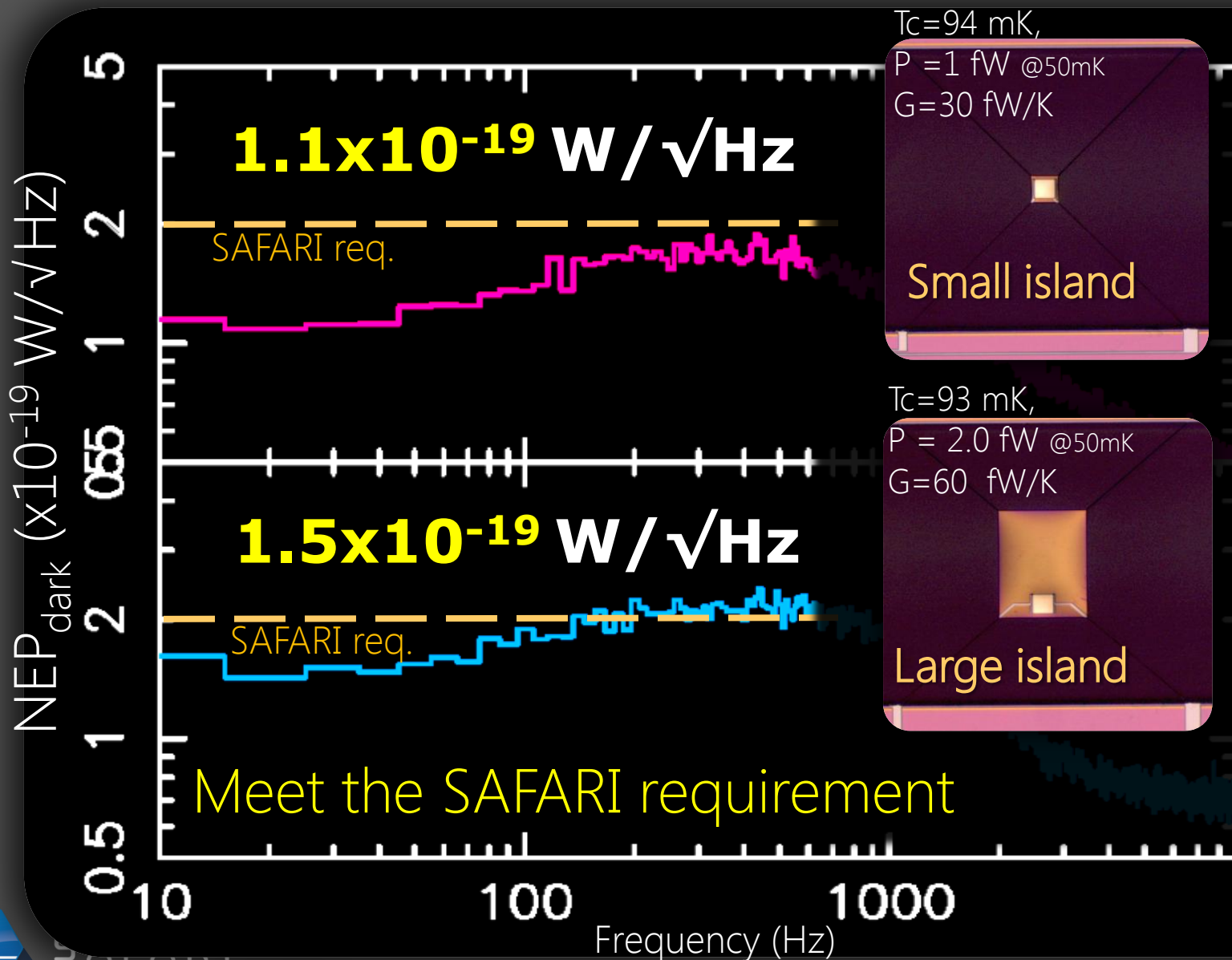


10pix-FDM system
 1-3 MHz resonators
 $df=100$ kHz

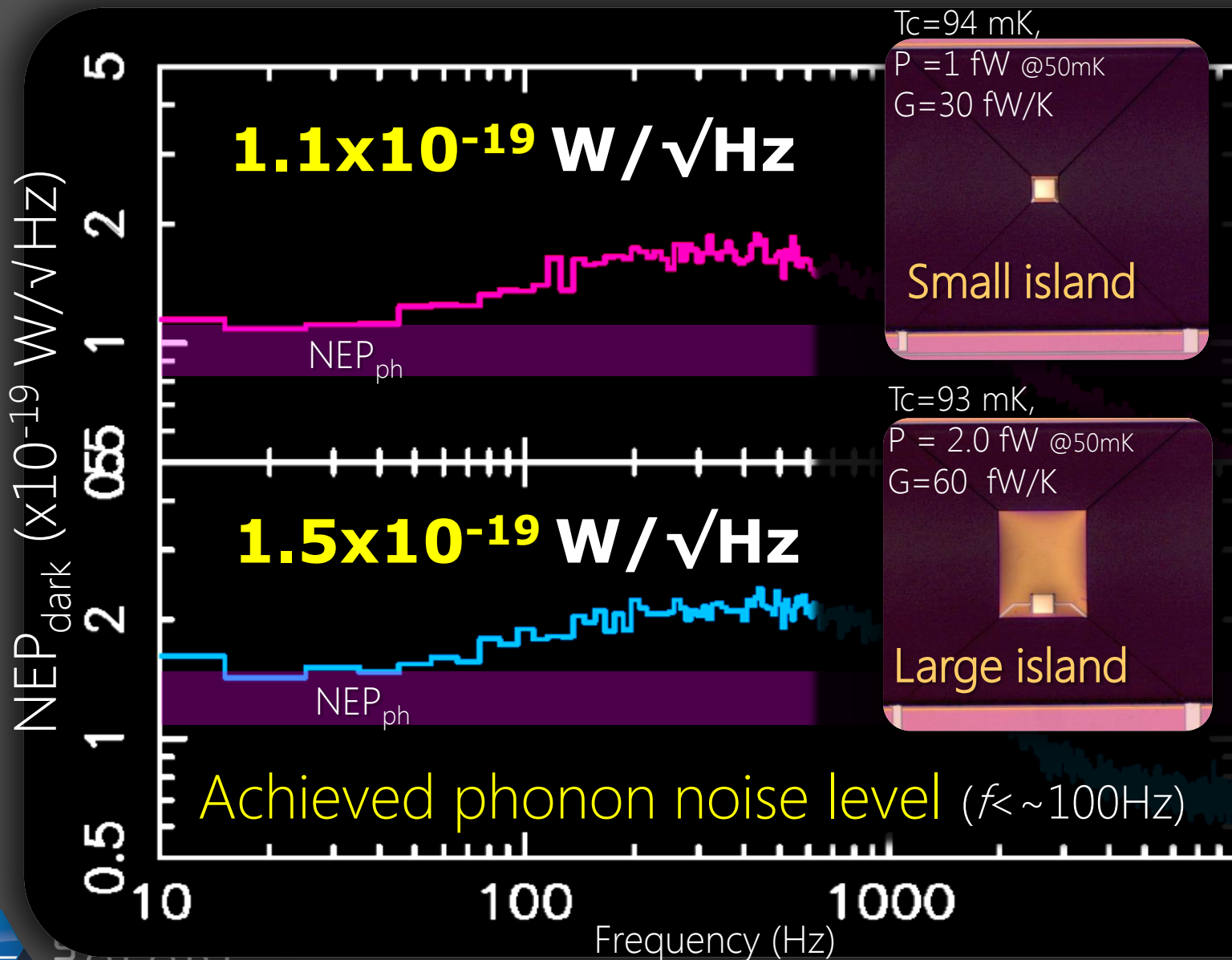
Measured thermal conductance



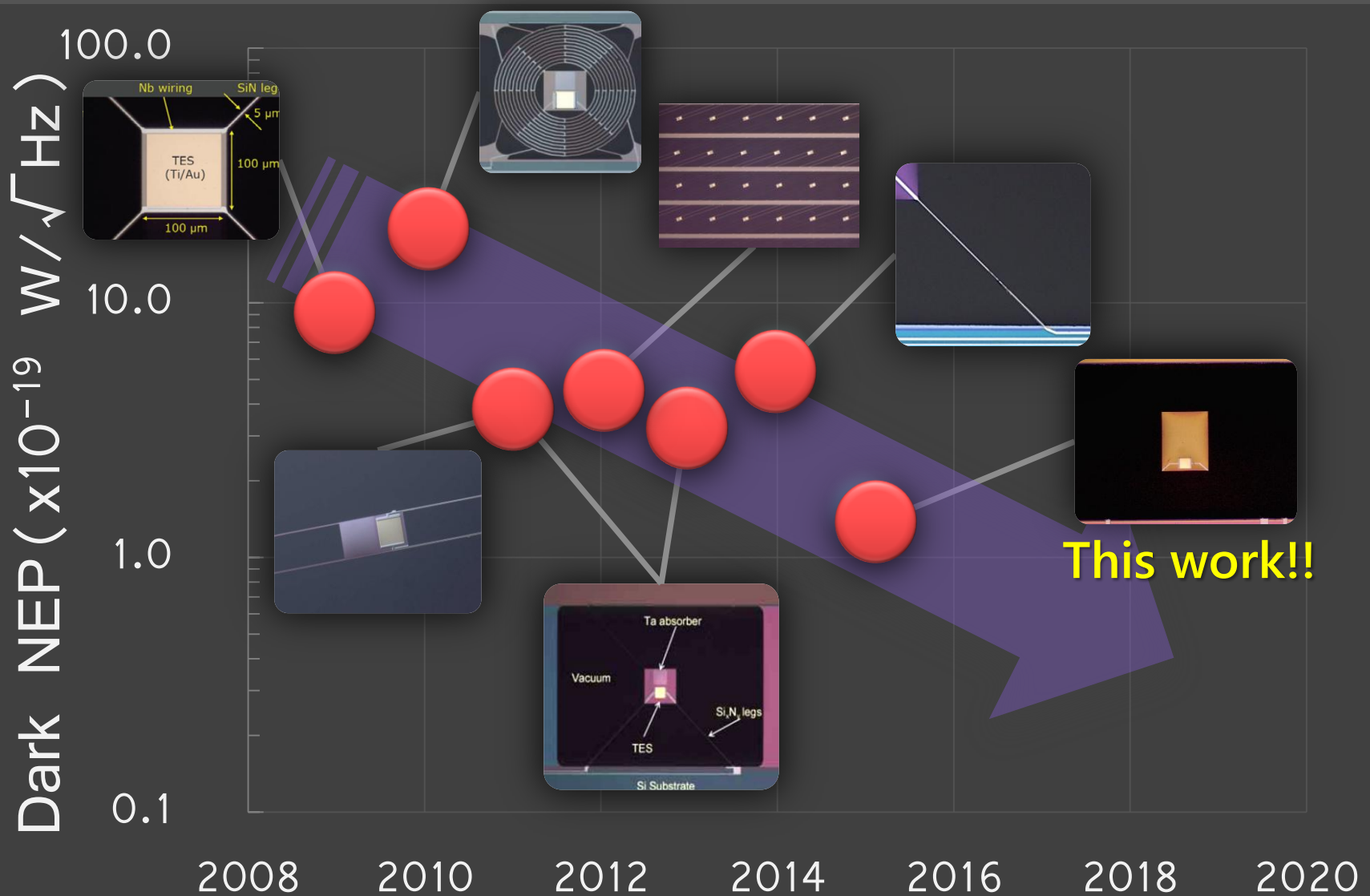
Measured NEPs



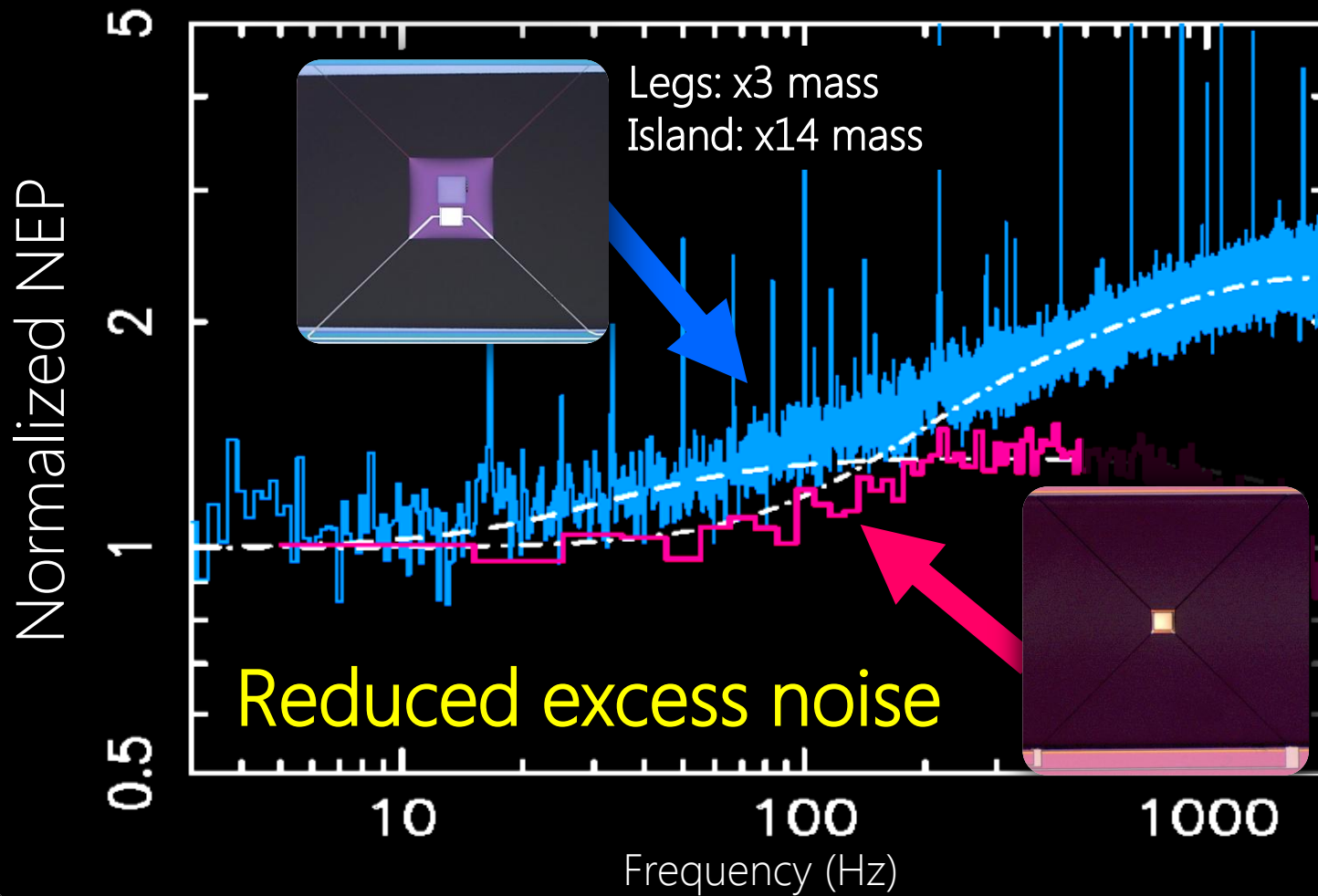
Measured NEPs



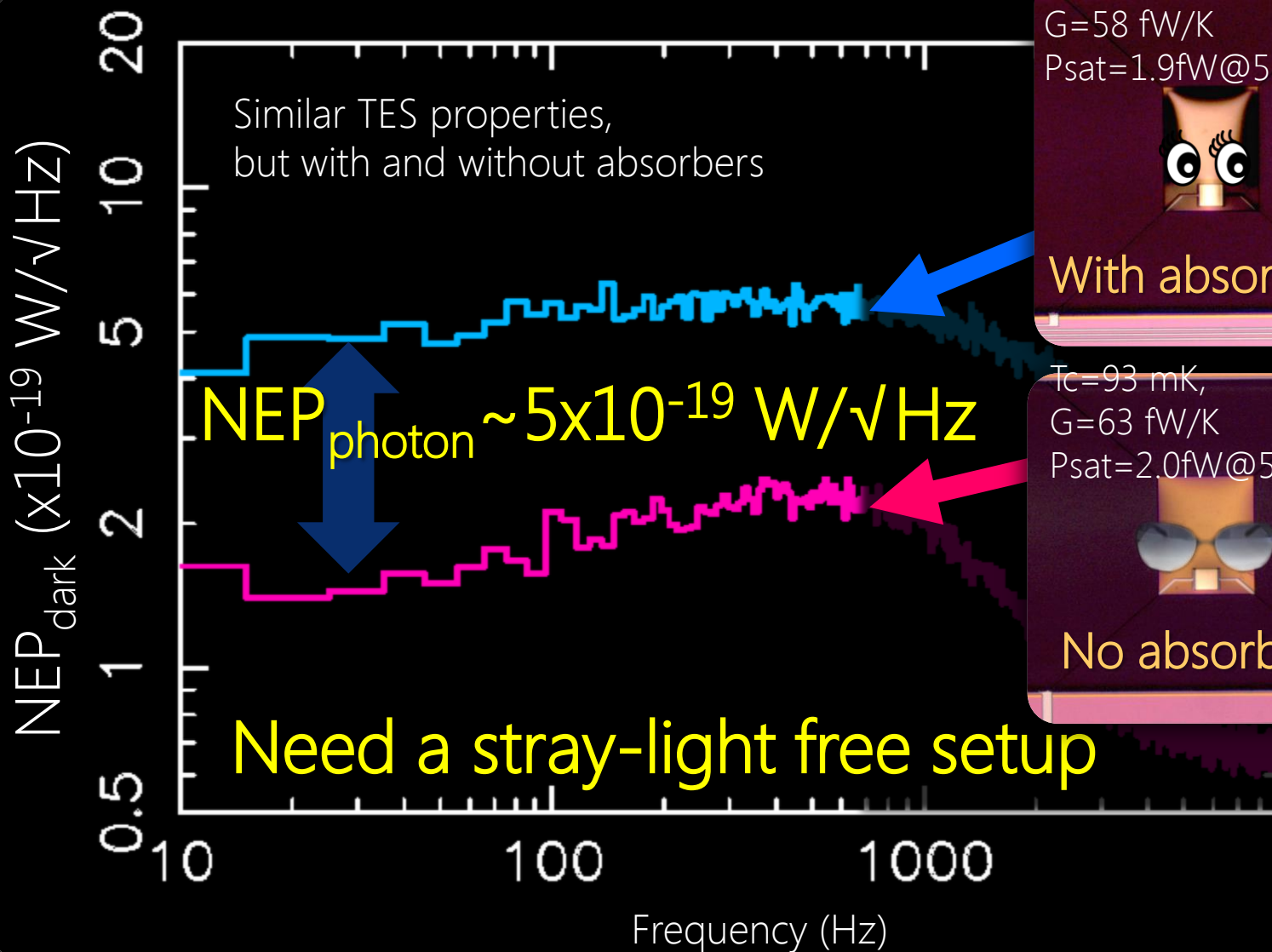
NEP-evolution track of SRON TESs



Excess noise



Darkness of current setup



Tc=87 mK,
G=58 fW/K
Psat=1.9fW@50mK



With absorber

Tc=93 mK,
G=63 fW/K
Psat=2.0fW@50mK



No absorber



SAFARI

SRON



Summary

Ultra-low G TESs were fabricated by DRIE

- Without an absorber

We measured an electrical NEP as low as 1.1×10^{-19} W/ $\sqrt{\text{Hz}}$, which achieved the **phonon noise limit**, and also a reasonable response speed (**<1 msec**).

- With an absorber

We confirmed a higher NEP ($\sim 5 \times 10^{-19}$) due to stray light.